ABSTRACT OF THE DISCLOSURE

In a method of producing a semiconductor laser apparatus, a conductive die-bonding paste is applied to a bonding surface in a predetermined position thereof and then preheated at a temperature equal to or higher than a temperature at which a diluent of the conductive die-bonding paste starts to transpire, but lower than a temperature at which the conductive die-bonding paste starts a thermosetting reaction. Then, with a semiconductor laser chip placed on the preheated conductive die-bonding paste, the latter is heated to be hardened. In the thus produced semiconductor laser apparatus, a highest position at which the conductive die-bonding paste adheres to end surfaces of the semiconductor laser chip is at a height of more than 0.01 mm from the bonding surface, but is below light-emitting points of the semiconductor laser chip.